

## Tuning the phonon transport in bilayer graphene to an anomalous regime dominated by electron-phonon scattering

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Recent studies have revealed the significance of electron-phonon interaction (EPI) in phonon transport at intermediate temperatures. In some metals, the EPI can even dominate over the anharmonic phonon-phonon (ph-ph) scattering, leading to an anomalous phonon transport regime in which the lattice thermal conductivity  $\kappa_L$  becomes nearly temperature ( $T$ ) independent in contrast to the usual  $1/T$  dependence. However, the experimental verification of this anomalous transport regime is very challenging due to the difficulty in separating the phonon contributions from the dominating electron ones to the measured total thermal conductivity in metals. In this work, using first-principles calculations, we predict that in bilayer graphene, the phonon transport can be driven to the anomalous regime by tuning the doping level. At high doping levels close to the Van Hove singularity, the EPI can result in a fivefold reduction of  $\kappa_L$  at room temperature, and  $\kappa_L$  becomes  $T$  independent. This anomalous behavior is found to have its origin in three aspects: (i) mirror symmetry breaking enables direct coupling between flexural phonons, the dominant carriers of  $\kappa_L$ , and electrons; (ii) dominance of normal processes in the anharmonic ph-ph scattering facilitates the EPI to be more prominent; (iii) dominance of these normal ph-ph processes induces the indirect effect of EPI on  $\kappa_L$ . This is distinct from monolayer graphene, where the mirror symmetry prohibits the direct scattering of the flexural phonons by electrons and only the indirect EPI affects  $\kappa_L$ . This work gives insight into the manipulation of heat conduction via externally induced EPI in two-dimensional materials in which mirror symmetry breaks and normal processes dominate the ph-ph scattering.

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The electron-phonon interaction is a fundamental quantity in condensed matter physics, essential for many physical properties including electrical transport, superconductivity, and optical absorption [1–3]. While the effect of the electron-phonon interaction (EPI) on electrical transport has been extensively studied, its impact on phonon transport, especially in nonmetals, was rarely explored, as the EPI was long believed to affect phonon transport only at very low temperatures. Only recently the EPI has been identified to have a significant role in lattice thermal conductivity in certain materials even at room temperature (RT). Liao *et al.* predicted [4] that, by adjusting the carrier concentration  $n$ , the EPI can result in up to 45% reduction of  $\kappa_L$  in heavily doped silicon even at RT, pioneering first principles investigation of the EPI effect on  $\kappa_L$ . This effect was subsequently observed experimentally [5]. It was also found that the phonon-electron (ph-e) scattering is much stronger than the phonon-phonon (ph-ph) scattering in a few transition metal carbides and the group-VI metals [6–9], giving rise to an anomalous phonon transport regime in which  $\kappa_L$  is nearly  $T$  independent. It is important to note that usually the electronic contribution dominates the thermal conductivity in metals and that it is difficult to separate the phononic and electronic contributions. These

make the experimental verification of the anomalous regime very challenging. Furthermore, the EPI is an intrinsic and thus unadjustable scattering mechanism in metals. In contrast, the EPI in nonmetals, serving as an extrinsic scattering mechanism, can be largely tuned by changing carrier concentration. However, though EPI can play an important role, it has been found not strong enough to lead to the anomalous transport behavior in realistic systems so far, e.g., a reduction of less than 50% and a nonweak  $T$  dependence of thermal conductivity ( $\kappa_L \propto T^{-\alpha}$ ,  $\alpha > 0.6$ ) in  $p$ -type Si [4],  $n$ -type 3C-SiC [10], and  $p$ -type silicene [11]. In this context, whether the anomalous phonon transport regime can be achieved in a realistic system by manipulating the carrier concentration is of great importance not only from the fundamental point of view but also for practical applications.

Graphene, a representative of two-dimensional (2D) semimetals, has attracted much attention because of its record-high  $\kappa_L$  [12,13]. Despite intensive efforts to study phonon transport in MLG and the fact that high charge carrier densities of  $|n| > 5.5 \times 10^{14} \text{ cm}^{-2}$  can be achieved by fabricating electrolytic and ionic-liquid gates [14–18], the effect of EPI on its  $\kappa_L$ , however, had never been studied, as the EPI was thought to have little effect on its  $\kappa_L$  due to the fact that the flexural acoustic (ZA) phonons, the dominant carriers of  $\kappa_L$ , cannot interact with electrons directly due to the mirror symmetry [19]. Notably, our recent *ab initio* study [20] has

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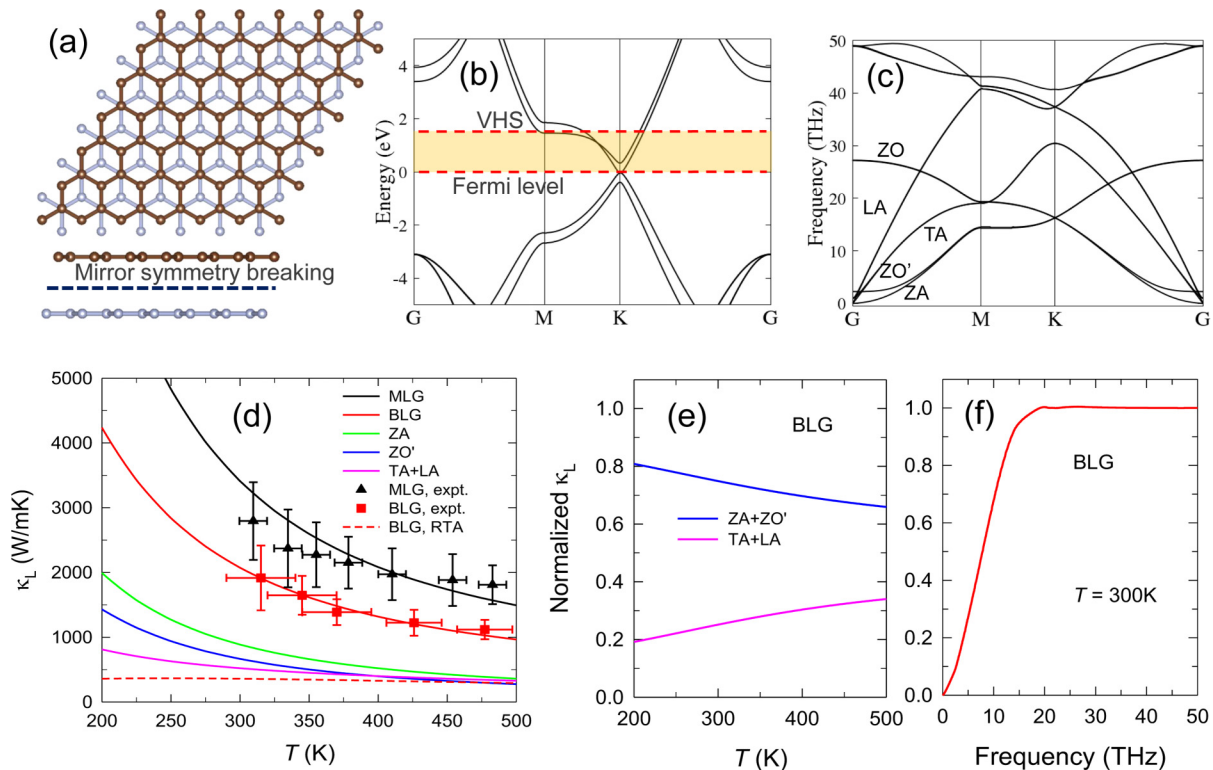


FIG. 1. (a) The side and top views of the lattice structure of *AB*-stacked BLG, with different colors labelling different layers. (b) The electronic structure of BLG, with the orange shading representing the range of Fermi levels tuned by the carrier density. (c) The phonon dispersion of BLG. ZA denotes the flexural acoustic phonons, and ZO' and ZO represent the flexural optical phonons. TA and LA denote the transversal and longitudinal acoustic modes, respectively. (d)  $T$ -dependent  $\kappa_L$  for pristine MLG and BLG. (e) The relative contributions from the flexural phonons (ZA + ZO') and other acoustic phonons (TA + LA). (f) The normalized cumulative  $\kappa_L$  at 300 K.

demonstrated that although the ZA phonons cannot be scattered by electrons directly, the indirect interaction between the ZA phonons and electrons enables 21% reduction of  $\kappa_L$  at RT in *n*-doped monolayer graphene (MLG). The excellent thermal transport behavior persists in bilayer graphene (BLG). Although the  $\kappa_L$  of BLG is significantly reduced compared with MLG due to the cross-plane coupling of phonons induced by the van der Waals (vdW) interactions between layers [21,22], recent studies [21,23–25] have shown that the  $\kappa_L$  of BLG is still as high as  $\sim 2000$  W/mK, comparable to diamond [26]. It is also important to note that, distinct from MLG, the flexural phonons in *AB*-stacked BLG can be directly scattered by electrons due to the mirror symmetry breaking with respect to the basal plane, as seen in Fig. 1(a). The EPI is thus expected to have stronger effect on  $\kappa_L$  in BLG than in MLG.

In this Letter, by performing density functional calculations, we predict that the EPI can lead to the anomalously weak  $T$  dependence and a large reduction (up to fivefold) of  $\kappa_L$  at high doping levels in *AB*-stacked BLG, enabling the experimental verification of the EPI-induced anomalous phonon transport regime. Such an ultrastrong effect is found to originate from the direct coupling between the flexural phonons and electrons induced by the mirror symmetry breaking, together with the dominance of normal ph-ph scattering.

Here the thermal conductivity is calculated by exactly solving the phonon Boltzmann transport equation (BTE) using an iterative scheme starting with the relaxation time approx-

imation (RTA), and phonon lifetimes due to the isotope, anharmonic three-phonon, and ph-e scatterings are included. See more details in Sec. 1 of the Supplemental Material [27] (see, also, Refs. [9,28–34] therein).

Solving the BTE requires electron energies, phonon frequencies, and anharmonic interatomic force constants, which were calculated from density-functional theory and density-functional perturbation theory, as implemented in the QUANTUM-ESPRESSO package [35]. The EPW package [36] was employed to calculate the ph-e scattering rates. The SHENG-BTE package [28,37,38] was modified to incorporate the ph-e scattering rates and then used to solve the BTE. Full computational details are shown in Sec. 2 of the Supplemental Material [27] (see, also, Refs. [39–42] therein).

We first study the intrinsic thermal transport properties of BLG. Our calculated phonon dispersion of BLG is presented in Fig. 1(d). It clearly shows that the interlayer vdW interaction causes the the original ZA mode to split into the ZA and ZO' modes, with the latter being a so-called layer breathing mode [43,44] and corresponding to the out-of-plane relative motion of atoms. Due to the splitting, the ZA branch of BLG in the long-wave limit ( $\mathbf{q} \rightarrow \mathbf{0}$ ) is no longer strictly quadratic [45]. As a consequence, the four-phonon scattering in BLG should be unimportant as demonstrated in Ref. [46], and hence in the present work we consider phonon anharmonicity only up to the third order. Also, the existence of the breathing mode could bring in more three-phonon scattering channels

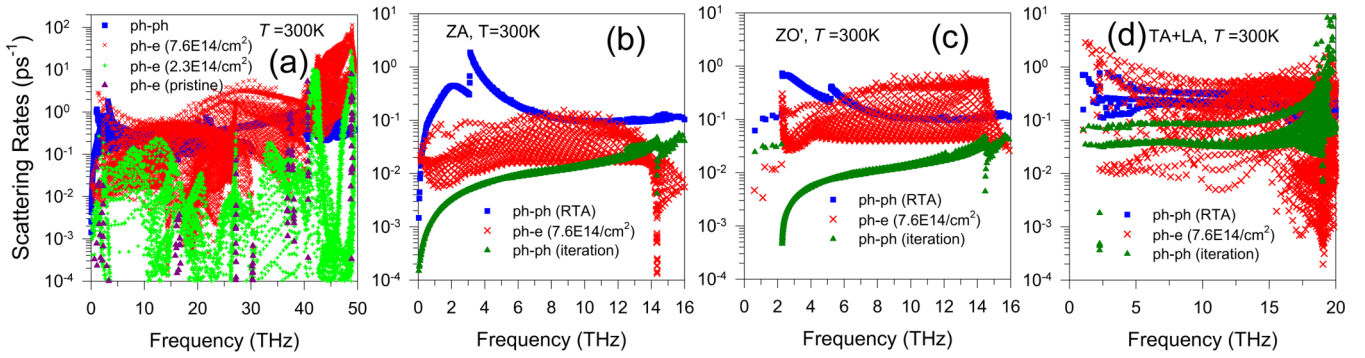


FIG. 2. (a) Comparison of the intrinsic ph-ph and ph-e scattering rates at different carrier densities in BLG at 300 K, calculated within the RTA. Comparison of ph-ph and ph-e scattering rates of (b) ZA, (c) ZO', and (d) TA and LA modes for phonons below 20 THz in doped BLG with  $n = 7.6 \times 10^{14} \text{ cm}^{-2}$ . Both the ph-ph scattering rates determined by the RTA and by the exact solution are provided.

involving ZA phonons, implying the stronger three-phonon scattering of ZA modes for BLG than for MLG.

Figure 1(d) shows the  $T$ -dependent  $\kappa_L$  for pristine MLG and BLG. Our calculations show reasonable agreement with the measured data [47]. It can be seen that with one layer added, the  $\kappa_L$  at RT decreases from  $\sim 3412$  to  $2073 \text{ W/mK}$ , by over 29%. Also shown is the  $\kappa_L$  calculated within the RTA for BLG, which is significantly lower than the exact values from the iterative solution over the entire  $T$  range. The severe underestimation of  $\kappa_L$  by the RTA signifies the dominance of momentum-conserved normal processes over umklapp processes in the ph-ph scattering of BLG. By further decomposing  $\kappa_L$  into different branches, we can see that below 400 K the  $\kappa_L$  is always dominated by the ZA and ZO' branches. To examine this more fully, in Fig. 1(f) we show the relative contributions to  $\kappa_L$  from the ZA and ZO' modes ( $\kappa_L^{\text{ZA+ZO'}}$ ) and other acoustic modes ( $\kappa_L^{\text{TA+LA}}$ ). It is evident that  $\kappa_L^{\text{ZA+ZO'}}$  gives the dominant contribution over the entire  $T$  range. At RT,  $\kappa_L^{\text{ZA+ZO'}}$  provides 75% of the total  $\kappa_L$ , and  $\kappa_L^{\text{TA+LA}}$  gives  $\sim 25\%$ . Figure 1(g) also displays the cumulative  $\kappa_L$  of BLG, which indicates that the  $\kappa_L$  is determined by phonons with frequency below 20 THz.

In the pristine case, the effect of EPI on the  $\kappa_L$  of BLG is negligible, as only some phonons around  $\Gamma$  and  $\mathbf{K}$  characterized by certain discrete frequencies can be scattered by electrons, similarly as in MLG [20]. As is seen in Fig. 2(a), in the neutral BLG, the ph-e scattering rates are considerably lower than the intrinsic ph-ph scattering rates. Recent studies have shown that high doping levels close to or even beyond the Van Hove singularity (VHS) [corresponding to the upper bound of the shading region in Fig. 1(c)] can be achieved [14–18]. In the doping case, more electrons are able to efficiently participate in the ph-e scattering processes, and consequently the region in the Brillouin zone (BZ) where phonons can be scattered broadens around  $\Gamma$  and  $\mathbf{K}$ . From Fig. 2(a), it is clear that the ph-e scattering rates significantly increase with  $n$ , and phonons in the whole BZ can be scattered by electrons above  $n = 2.3 \times 10^{14} \text{ cm}^{-2}$ . For the case of  $n = 7.6 \times 10^{14} \text{ cm}^{-2}$  (corresponding to the VHS) in particular, the ph-e scattering rates for phonons with frequency below 20 THz, which have a major contribution to  $\kappa_L$ , are comparable to or even higher than the ph-ph scattering rates.

Since the  $\kappa_L$  of BLG is determined by the ZA, ZO', as well as TA and LA phonons, we further compare the scattering rates due to ph-e and ph-ph scatterings for these modes. The results are given in Figs. 2(b)–2(d). Unlike MLG, the flexural phonons in BLG can be directly scattered by electrons owing to the mirror symmetry breaking. As is seen in Figs. 2(b) and 2(c), when  $n$  reaches  $7.6 \times 10^{14} \text{ cm}^{-2}$ , the ph-e scattering rates of ZA and ZO' modes are comparable to or even surpass their ph-ph scattering rates. As for the TA and LA modes, the scattering rates of phonons with frequency below 20 THz are dominated by ph-e scattering, as seen in Fig. 2(d).

As mentioned above, the large discrepancy between the RTA and iteration reveals the dominance of normal ph-ph scattering in BLG. Hence, the intrinsic ph-ph scattering given by the RTA is significantly stronger than that given by the iterative solution to the BTE. As is seen in Figs. 2(b)–2(d), the ph-e scattering rates of ZA and ZO' as well as TA and LA modes are substantially larger than the ph-ph scattering rates from the iterative solution. This indicates that the EPI may dominate the thermal transport of BLG at high doping levels.

The calculated  $T$ -dependent  $\kappa_L$ s of BLG for several carrier densities as well as the pristine case are shown in Fig. 3(a). It clearly shows that the EPI can tune the phonon transport of BLG to an anomalous regime. Interestingly, at high carrier densities, e.g.,  $n = 7.6 \times 10^{14} \text{ cm}^{-2}$ , the  $\kappa_L$  is found to be almost independent of  $T$  (exactly  $\kappa_L \sim T^{-0.078}$ ), deviating from the  $T^{-1}$  law governed by three-phonon scattering. The ph-e scattering is nearly  $T$  independent because of the almost  $T$ -independent term of  $f_{k_i} - f_{(k+q)_j}$  in the formula of EPI [see Eq. (S5) in the Supplemental Material [27]], with  $f_{k_i}$  being the Fermi-Dirac distribution function with band branch  $i$  and wave vector  $\mathbf{k}$ . Therefore, this anomalous weak  $T$  dependence of  $\kappa_L$  is due to the predominance of the nearly  $T$ -independent ph-e over the  $T$ -dependent ph-ph scattering, which has been reported in some metals [6,7] but not in nonmetals yet. To look into the carrier dependence more closely, the RT  $\kappa_L$  varying with a series of carrier densities are given in Fig. 3(b). It is found that when  $n$  is below  $7.8 \times 10^{13} \text{ cm}^{-2}$ , the EPI effect on  $\kappa_L$  is negligible, whereas the EPI leads to significant reduction of lattice thermal conductivity as  $n$  reaches above  $1.4 \times 10^{14} \text{ cm}^{-2}$ . Remarkably, when  $n$  is as high as  $7.6 \times 10^{14} \text{ cm}^{-2}$ , the EPI decreases the  $\kappa_L$  from  $\sim 2073 \text{ W/mK}$  in the pristine case to  $\sim 400 \text{ W/mK}$  at RT, by 80%. This exceptionally strong EPI effect on  $\kappa_L$  has

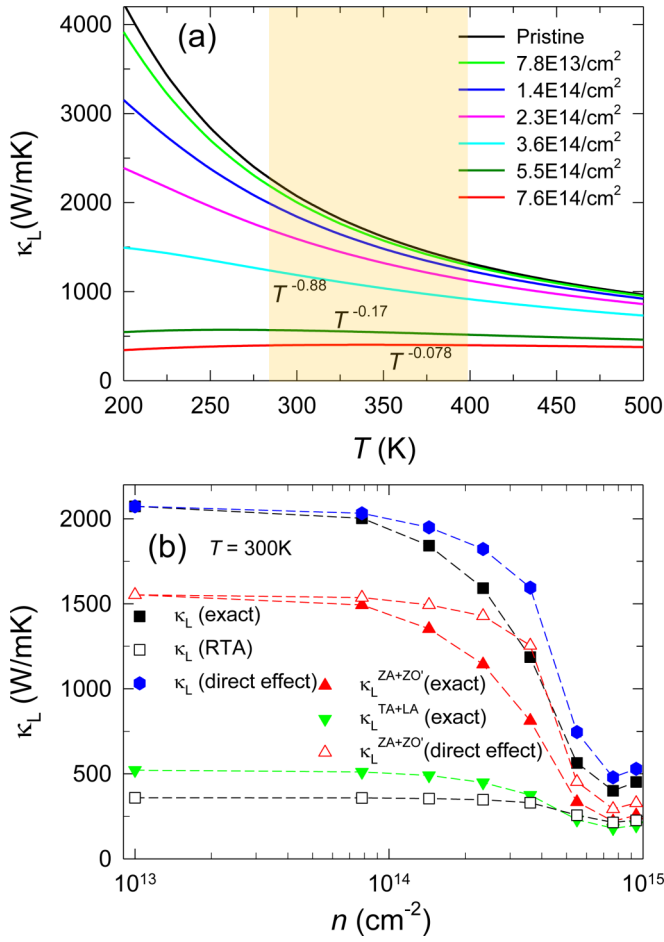


FIG. 3. (a) The calculated  $T$ -dependent  $\kappa_L$  of BLG at different carrier densities. (b) The values of  $\kappa_L$ ,  $\kappa_L^{ZA+ZO'}$ , and  $\kappa_L^{TA+LA}$  determined from the exact BTE solution, and  $\kappa_L$  from the RTA as a function of  $n$  at RT. To highlight the direct EPI effect, the  $\kappa_L$  and  $\kappa_L^{ZA+ZO'}$  calculated within the BTE in which ph-e processes are not included in the iteration are also shown.

its origin in direct interaction between flexural phonons and electrons, weak ph-ph scattering enabled by strong normal scatterings, and indirect coupling between flexural phonons and electrons, which will be elaborated in detail in the following.

First, we look into the EPI effect on thermal conductivity at the RTA level in Fig. 3(b). In the case of  $n = 7.6 \times 10^{14}$  cm $^{-2}$ , within the RTA the EPI reduces  $\kappa_L$  by 41% at RT, much lower than the actual reduction given by the iterative solution. As the dominant contributors of  $\kappa_L$ , the flexural phonons' contributions are obviously suppressed by the direct coupling between flexural phonons and electrons enabled by the mirror symmetry breaking, e.g.,  $\kappa_L^{ZA}$  is decreased from 68 to 51 W/mK at RT, by 25%, as seen in Table I. This is completely different from MLG, where  $\kappa_L^{ZA}$  cannot be affected by the EPI due to the mirror symmetry [20]. In fact, the RTA improperly treats the normal ph-ph scatterings as fully resistive processes, thus it overestimates the intrinsic ph-ph scattering and consequently underestimates the EPI effect on  $\kappa_L$ . To quantify the EPI effect more accurately, a natural way is to calculate the total phonon lifetime by directly summing up

TABLE I. The calculated  $\kappa_L$  and contributions from different branches for the pristine and doped ( $n = 7.6 \times 10^{14}$  cm $^{-2}$ ) BLG at RT, predicted from the RTA and the iterative solution, respectively.

$\kappa_L$ (W/mK)	Pristine		$n = 7.6 \times 10^{14}$ cm $^{-2}$	
	RTA	Iteration	RTA	Iteration
ZA	68	887	51	139
ZO'	61	666	30	82
TA+LA	213	518	125	175
Total	360	2073	214	400

the ph-ph scattering rates given by the iterative solution and ph-e scattering rates, with the details given in Sec. 1 of the Supplemental Material [27]. We then apply this approximation to evaluate the EPI effect, as shown in Fig. 3(b), and find that the EPI can reduce the  $\kappa_L$  by 77%, still lower than the actual reduction. The underestimation of 3% is due to the fact that this approach cannot incorporate the indirect EPI effect, which is important when normal processes dominate. Actually, in MLG there exists only indirect effect between the ZA phonons and electrons mediated by the TA and LA phonons, leading to 21% reduction of  $\kappa_L$  [20]. Note that this approximation has been utilized recently [48,49].

To simultaneously include the indirect effect of EPI, only an iterative solution is appropriate. Note that since each ph-e scattering process involves one phonon only, the iterative form of the BTE after including EPI is the same as it is without including EPI (see Sec. 1 of the Supplemental Material [27]). With the indirect EPI effect included through the iterative scheme, we show that the EPI leads to 80% reduction of  $\kappa_L$ . As seen in Fig. 3(b), the indirect EPI effect is reflected in the difference of thermal conductivity ( $\kappa_L$  and  $\kappa_L^{ZA+ZO'}$ ) obtained from these two approaches. Specifically, the direct EPI effect alone reduces the  $\kappa_L^{ZA+ZO'}$  by 81% and after including the indirect effect the  $\kappa_L^{ZA+ZO'}$  is reduced by 85%. Also, we can see from Table I that the reduction of contributions from different branches due to the EPI after the iteration is several times larger than before the iteration. This indicates that the dominance of normal ph-ph scatterings plays a key role in achieving such an ultrastrong EPI effect on  $\kappa_L$  by magnifying the direct EPI effect and introducing the indirect EPI effect.

The present results emphasize the significance of externally induced EPI in suppressing the  $\kappa_L$  of BLG. We have to point out that such an ultrastrong effect is not limited to graphene but should be universal in many other 2D materials such as h-BX ( $X = N, P,$  and  $As$ ) and h-AlN [50,51], for which (i) flexural phonons give a major contribution to  $\kappa_L$ ; (ii) normal processes dominates the ph-ph scattering. This is quite different from materials like silicon [4] and silicene [11], for which even at high carrier density limit the EPI decreases  $\kappa_L$  by less than 50%, as the dominance of umklapp processes makes the ph-ph scattering always stronger than the ph-e scattering. Note also that in the present work the  $\kappa_L$  is calculated within the decoupled BTE, where electrons are taken to be in equilibrium when solving the BTE, and the electron drag effect is thus not included. As mentioned previously [52,53], the electron drag effect on the thermal conductivity is generally weak, since the drag effect only

affects the low-energy and zone-boundary phonons, which give the little contribution to  $\kappa_L$ . For MLG, it has been proven that umklapp processes dominate the e-ph scattering (electron scattering by phonons), which can bring quickly the electrons into equilibrium with the lattice, and the electron drag effect is thus negligible [20]. The same case also applies to BLG (see Sec. 4 of the Supplemental Material [27] and Refs. [54,55] therein).

To summarize, we have identified a marked EPI effect on the lattice thermal conductivity of BLG by first-principles calculations. Our results show that the EPI can result in the fundamentally different  $T$  dependencies of  $\kappa_L$ , and it can reduce the  $\kappa_L$  of BLG by as much as a factor of 5 even at RT. This is enabled by the combined effect of direct coupling between the flexural phonons and electrons induced by

the mirror symmetry breaking, as well as the dominance of normal ph-ph scattering. This EPI-driven anomalous phonon transport regime in BLG calls for the future experimental verification, and can be extended to other 2D materials.

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